

Abstract of the Disclosure

Disclosed is a method for fabricating a capacitor of a semiconductor device. The method comprises the steps of: forming a first interlayer insulating film on a substrate, and 5 then selectively removing the first interlayer insulating film to form a plug contact hole; forming a first contact plug; forming a first barrier layer; forming a first polysilicon layer and a second barrier layer; sequentially patterning the 10 second barrier layer, the first polysilicon layer, and the first barrier layer, thereby forming a first contact hole; forming a first dielectric layer; removing portions of the first dielectric layer, which are located at outside and bottom parts of the first contact hole, thereby leaving a portion of the first dielectric layer located at one side 15 portion of the first contact hole; forming a second polysilicon layer, and then removing the second polysilicon layer located at portions except for the first contact hole; forming a second dielectric layer, forming a third polysilicon layer, and patterning the third polysilicon layer; forming a 20 second interlayer insulating film, and selectively removing the second interlayer insulating film, the patterned third polysilicon layer, the second dielectric layer, the second barrier layer, and the first polysilicon layer, thereby forming a second contact hole; and forming a second contact

plug, and then forming a metal wiring.